Abstracts

L-Band Si Power V-FET

C. Xian-e, Z. Ping-hai and Q. Wen-rui. "L-Band Si Power V-FET." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 74-76.

A new structure Si vertical channel FET ---- the covered gate structure has been developed. Compared with the buried gate structure, an increasing power gain by more than 5 dB has been obtained. L-band devices with output power higher than 10W, power gain 6 dB at 1GHz have been fabricated. The relationship between the electrical properties and devices structure parameters are discussed. The excellent temperature performance and other characteristics are reported.

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